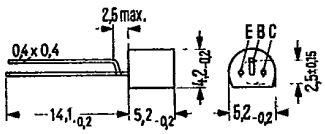
NPN Silicon RF Transistor

BF 562

SIEMENS AKTIENGESELLSCHAF !1 D

BF 562 is an NPN silicon RF transistor in TO 92 plastic package (10 A 3 DIN 41868). The transistor is particularly suitable for controllable VHF input stages in TV tuners.

Type	Ordering code
BF 562	Q62702-F542



Mounting instruction: Fixing hole dia 0.6
Approx. weight 0,25 g Dimensions in mm

Maximum ratings (T_{amb} = 25 °C)

Collector-emitter voltage	V_{CEO}	20	V
Collector-base voltage	V_{CBO}	30	V
Emitter-base voltage	V_{EBO}	3	V
Collector current	I_C	20	mA
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	–55 to +150	°C
Total power dissipation ($T_{amb} \leqq 45$ °C)	P_{tot}	250	mW

Thermal resistance

Junction to ambient air	R_{thJA}	≤420	K/W

Static characteristics (T_{amb} = 25 °C)

Base current			
(I_C = 3 mA; V_{CE} = 10 V)	I_B	≤150	µA
(I_C = 10 mA; V_{CE} = 7 V)	I_B	≤2	mA
Collecor-emitter breakdown voltage			
(I_C = 1 mA)	$V_{(BR)CEO}$	≥20	V
Collector-base breakdown voltage			
(I_C = 10 µA)	$V_{(BR)CBO}$	≥30	V
Emitter-base breakdown voltage			
(I_E = 10 µA)	$V_{(BR)EBO}$	≥3	V

Dynamic characteristics (T_{amb} = 25 °C)

Transition frequency			
(I_C = 2,5 mA; V_{CE} = 10 V; f = 100 MHz)	f_T	600	MHz
Power gain			
(I_C = 2,5 mA; V_{CE} = 10 V; f = 200 MHz; R_g = 60 Ω; R_L = 920 Ω)	G_{pb}	16	dB
Noise figure			
(I_C = 2,5 mA; V_{CE} = 10 V; f = 200 MHz; R_g = 60 Ω).	NF	3	dB
Reverse transfer capacitance			
(I_C = 1 mA; V_{CE} = 10 V; f = 1 MHz)	$-C_{12e}$	0,65	pF
Reverse transfer capacitance			
(V_{BE} = 0; V_{CB} = 10 V; f = 1 MHz)	$-C_{12b}$	0,12	pF

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